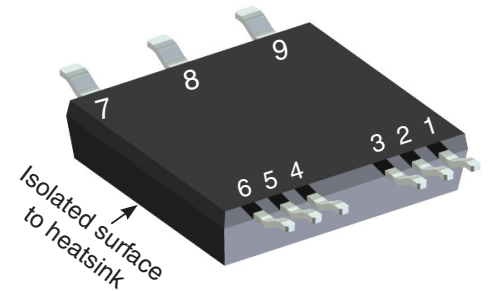


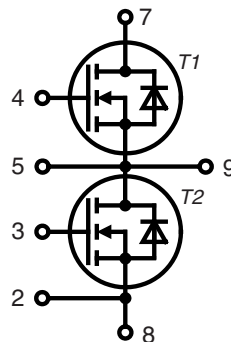
SiC Power MOSFET

$$\begin{aligned}
 I_{D25} &= 38 \text{ A} \\
 V_{DSS} &= 1200 \text{ V} \\
 R_{DS(on) \text{ max}} &= 52 \text{ m}\Omega
 \end{aligned}$$

Part number
 MCB30P1200LB



 E72873



Features / Advantages:

- High speed switching with low capacitances
- High blocking voltage with low $R_{DS(on)}$
- Easy to parallel and simple to drive
- Resistant to latch-up
- Real Kelvin source connection

Applications:

- Solar inverters
- High voltage DC/DC converters
- Motor drives
- Switch mode power supplies
- UPS
- Battery chargers
- Induction heating

Package: SMPD

- DCB isolated backside
- Isolation Voltage 2500 V
- Epoxy meets UL 94V-0
- RoHS compliant
- Advanced power cycling

Disclaimer Notice

Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.

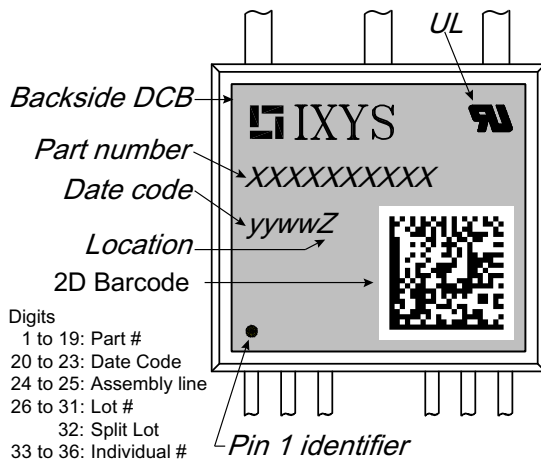
MOSFET				Ratings			
Symbol	Definitions	Conditions	min.	typ.	max.		
$V_{(BR)DSS}$	drain source breakdown voltage	$I_D = 100 \mu A$	1200			V	
$V_{GS(max)}$	max transient gate source voltage		-10		+25	V	
V_{GS}	continous gate source voltage	recommended operational value	-5		+20	V	
I_{D25} I_{D80} I_{D100}	drain current	$V_{GS} = 20 V$ $T_C = 25^\circ C$ $T_C = 80^\circ C$ $T_C = 100^\circ C$			38 30 27	A A A	
R_{DSon}	static drain source on resistance	$I_D = 40 A; V_{GS} = 20 V$ $T_{VJ} = 25^\circ C$ $T_{VJ} = 175^\circ C$		40 90	52	mΩ mΩ	
$V_{GS(th)}$	gate threshold voltage	$I_D = 10 mA; V_{GS} = V_{DS}$ $T_{VJ} = 25^\circ C$ $T_{VJ} = 175^\circ C$	2.0	2.6 2.0	4.0	V V	
I_{DSS}	drain source leakage current	$V_{DS} = 1200 V; V_{GS} = 0 V$ $T_{VJ} = 25^\circ C$		1	100	μA	
I_{GSS}	gate source leakage current	$V_{DS} = 0 V; V_{GS} = 20 V$ $T_{VJ} = 25^\circ C$			250	nA	
R_G	internal gate resistance	$f = 1 MHz; V_{AC} = 25 mV$, ESR of C_{ISS}		1.8		Ω	
C_{iss} C_{oss} C_{rss}	input capacitance output capacitance reverse transfer (Miller) capacitance	$V_{DS} = 1000 V; V_{GS} = 0 V; f = 1 MHz$ $T_{VJ} = 25^\circ C$		1895 150 10		pF pF pF	
Q_g Q_{gs} Q_{gd}	total gate charge gate source charge gate drain (Miller) charge	$V_{DS} = 800 V; I_D = 40 A; V_{GS} = -5/20 V$ $T_{VJ} = 25^\circ C$		115 28 37		nC nC nC	
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off}	turn-on delay time current rise time turn-off delay time current fall time turn-on energy per pulse turn-off energy per pulse	Inductive switching Free Wheeling Diode: Body Diode @ $V_{GS} = -5V$ $V_{DS} = 800 V; I_D = 40 A$ $V_{GS} = -5/20 V; R_G = 15 \Omega$ (external) $T_{VJ} = 25^\circ C$		25.5 11.1 85 23 0.92 0.48		ns ns ns ns mJ mJ	
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off}	turn-on delay time current rise time turn-off delay time current fall time turn-on energy per pulse turn-off energy per pulse	Inductive switching Free Wheeling Diode: Body Diode @ $V_{GS} = -5V$ $V_{DS} = 800 V; I_D = 40 A$ $V_{GS} = -5/20 V; R_G = 15 \Omega$ (external) $T_{VJ} = 150^\circ C$		23.5 9.8 93 25 1.0 0.4		ns ns ns ns mJ mJ	
R_{thJC} R_{thJH}	thermal resistance junction to case thermal resistance junction to heatsink	with heatsink compound; IXYS test setup		1.15	0.9	K/W K/W	

Source-Drain Diode				Ratings			
Symbol	Definitions	Conditions	min.	typ.	max.		
V_{SD}	forward voltage drop	$I_F = 20 A; V_{GS} = -5 V$ $T_{VJ} = 25^\circ C$ $T_{VJ} = 175^\circ C$		4.1 3.5		V V	
t_{rr} Q_{RM} I_{RM}	reverse recovery time reverse recovery charge (intrinsic diode) max. reverse recovery current	$V_{GS} = -5 V; I_F = 40 A$ $V_R = 800 V; -di_F/dt = 1000 A/\mu s$ $T_{VJ} = 25^\circ C$		55 285 15		ns nC A	

Note:

 When using SiC Body Diode the maximum recommended $V_{GS} = -5V$

Package SMPD			Ratings			
Symbol	Definitions	Conditions	min.	typ.	max.	
I_{RMS}	RMS current	wide terminal standard terminal			100 60	A A
T_{stg}	storage temperature		-55		150	°C
T_{op}	operation temperature		-55		150	°C
T_{vj}	virtual junction temperature		-55		175	°C
Weight				8		g
F_c	mounting force with clip		40		130	N
$d_{Spp/App}$	creepage distance on surface /	terminal to terminal	1.6			mm
$d_{Spb/Appb}$	striking distance through air	terminal to backside	4.0			mm
V_{ISOL}	isolation voltage	$t = 1$ second $t = 1$ minute		3000 2500		V V

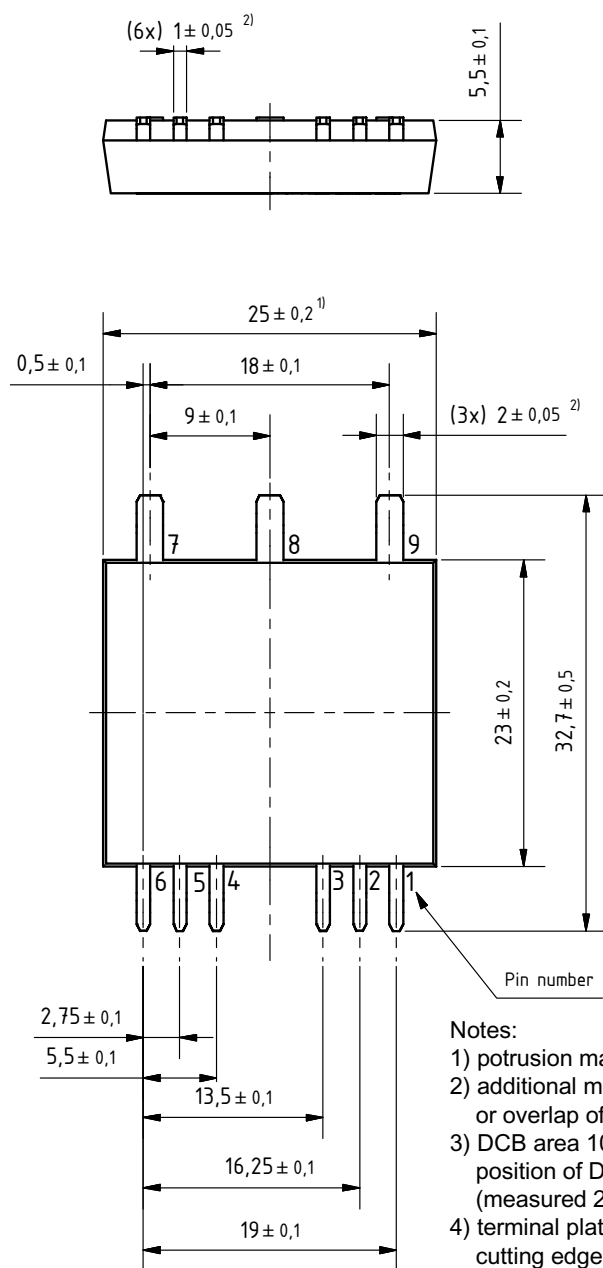

Part number

M = Mosfet
 C = SiC MOSFET
 B = Generation 2
 30 = Current Rating [A]
 P = Phase leg
 1200 = Reverse Voltage [V]
 LB = SMPD-B

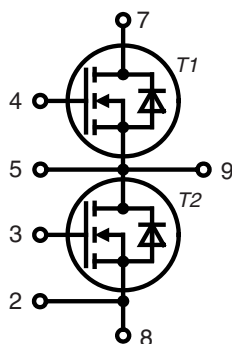
Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	MCB30P1200LB-TUB	MCB30P1200LB	Tube	20	MCB30P1200LB-TUB
Alternative	MCB30P1200LB-TRR	MCB30P1200LB	Tape&Reel	200	MCB30P1200LB-TRR

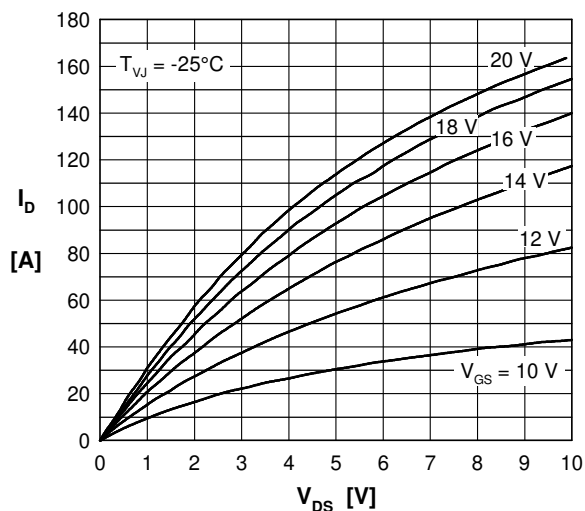
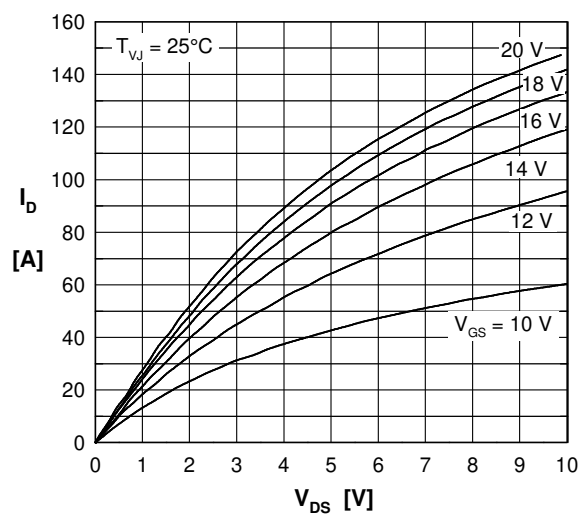
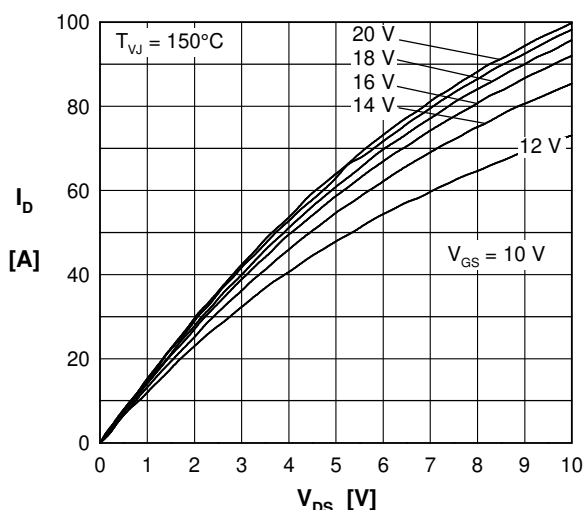
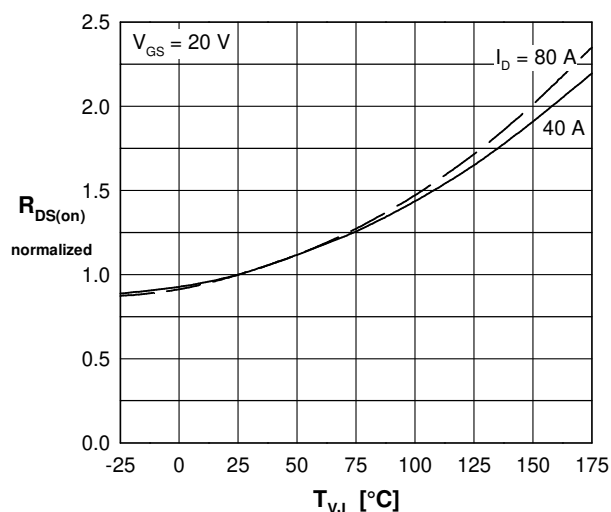
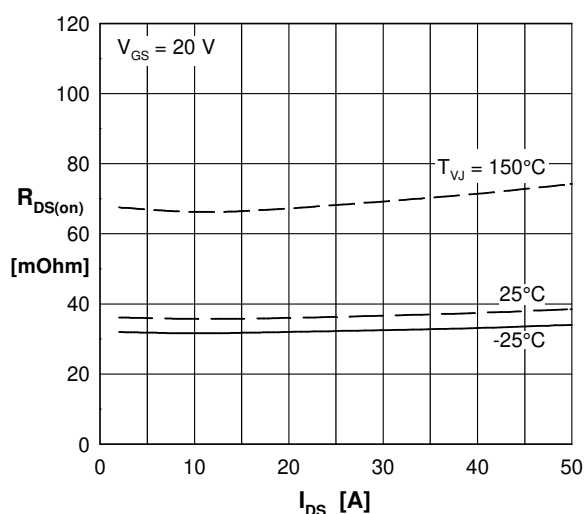
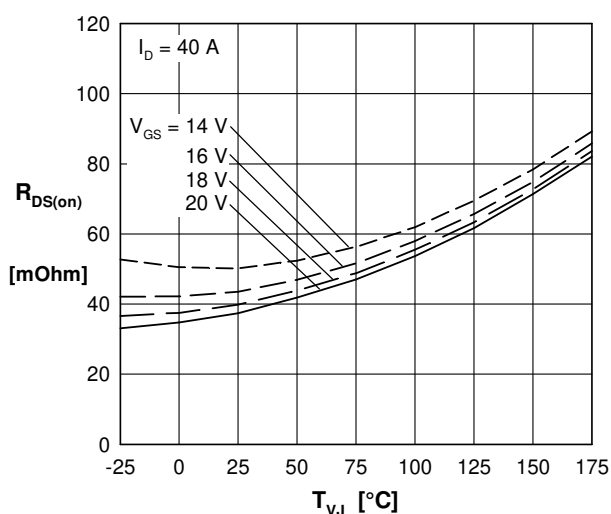
Outlines SMPD-B

Dimensions in mm (1 mm = 0.0394")


Notes:

- 1) potrusion may add 0.2 mm max. on each side
- 2) additional max. 0.05 mm per side by punching misalignment or overlap of dam bar or bending compression
- 3) DCB area 10 to 50 μm convex; position of DCB area in relation to plastic rim: $\pm 25 \mu\text{m}$ (measured 2 mm from Cu rim)
- 4) terminal plating: 2 - 6 μm Ni + 10 - 25 μm Sn (gal v.) cutting edges may be partially free of plating



Curves

 Fig. 1 Typical output characteristics (-25°C)

 Fig. 2 Typical output characteristics (25°C)

 Fig. 3 Typical output characteristics (150°C)

 Fig. 4 $R_{DS(on)}$ normalized vs. junction temperature T_{VJ}

 Fig. 5 $R_{DS(on)}$ versus drain current

 Fig. 6 $R_{DS(on)}$ versus junction temperature T_{VJ}

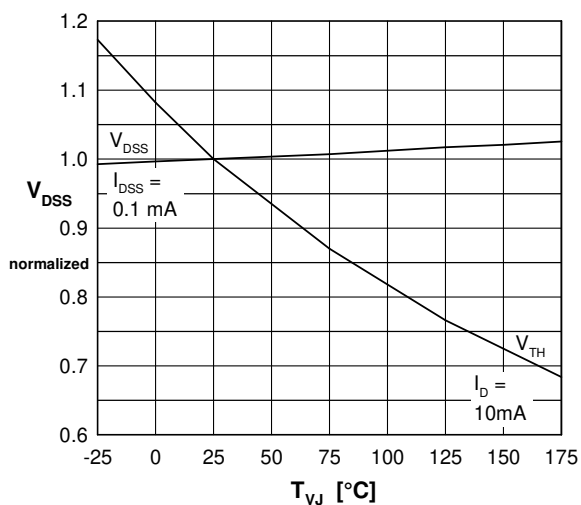
Curves


Fig. 7 Norm. breakdw V_{DSS} & treshhold voltage V_{TH} versus junction temperature T_{VJ}

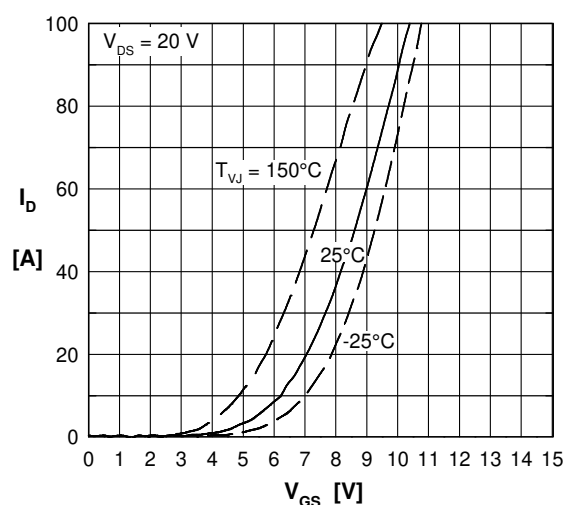


Fig. 8 Typical transfer characteristics

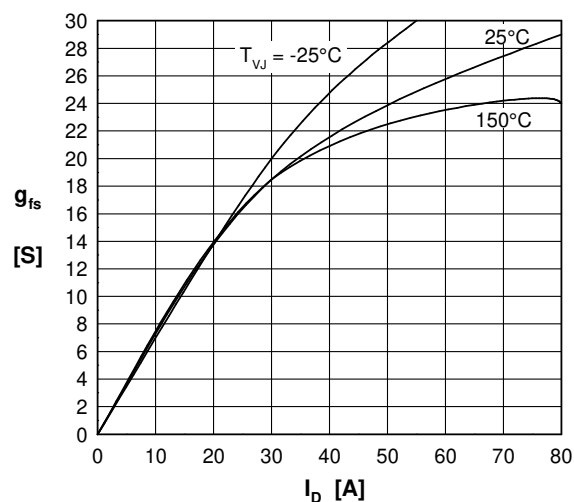


Fig. 9 Typical forward transconductance

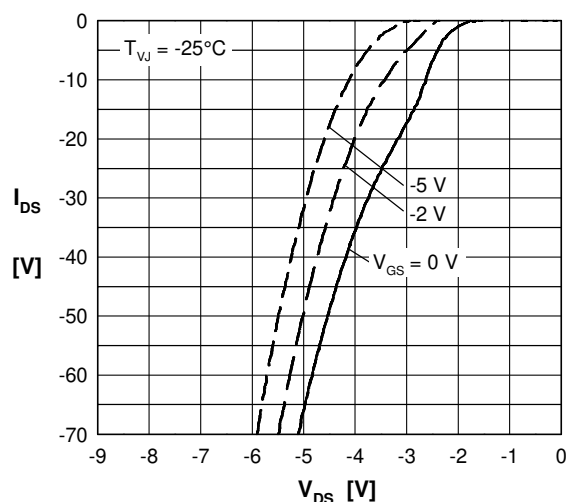


Fig. 10 Forward voltage drop of intrinsic diode versus V_{DS} measured at -55°C

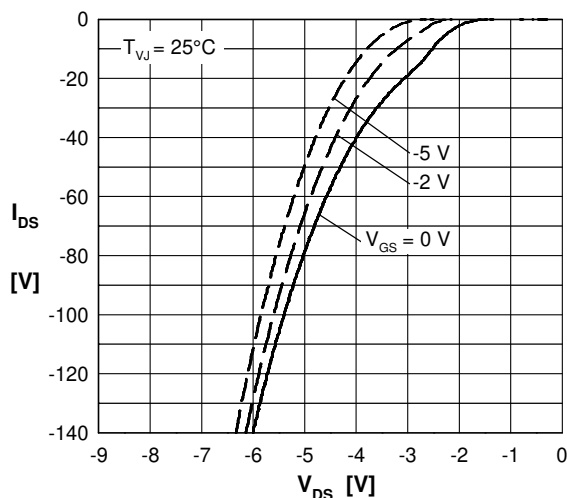


Fig. 11 Forward voltage drop of intrinsic diode versus V_{DS} measured at 25°C

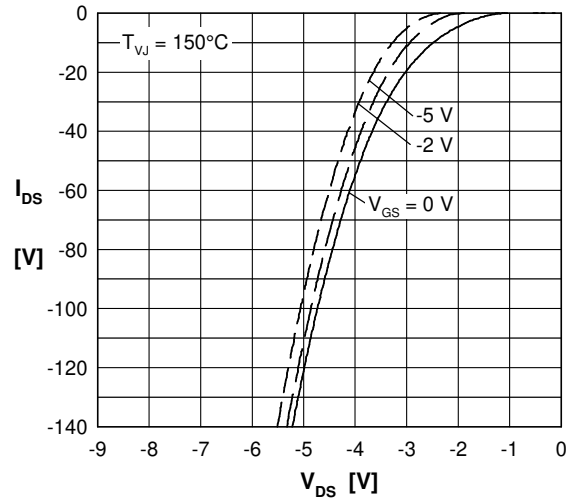


Fig. 12 Forward voltage drop of intrinsic diode versus V_{DS} measured at 150°C

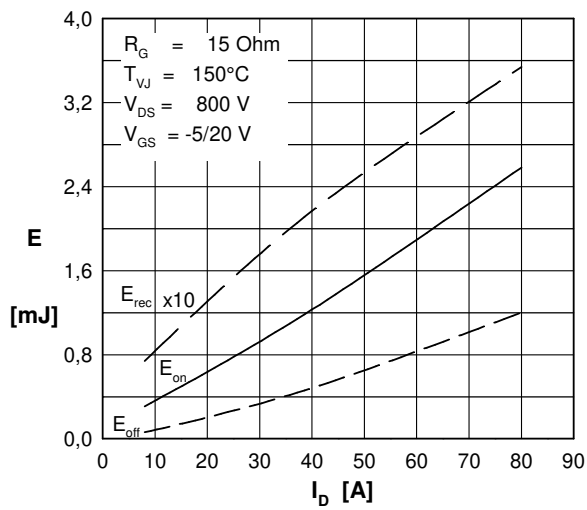
Curves


Fig. 13 Typical switching energy versus drain current

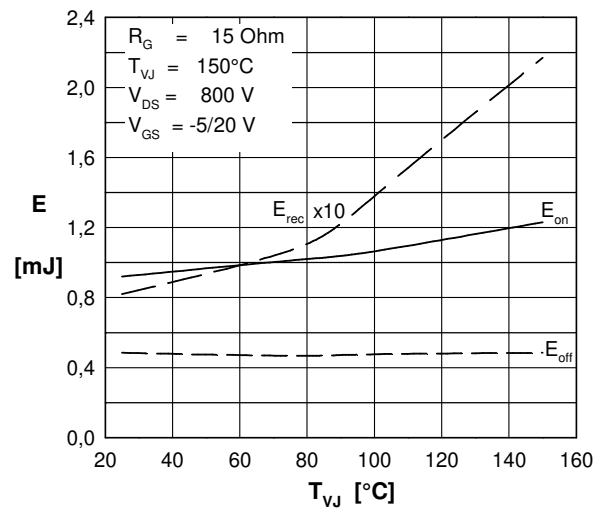


Fig. 14 Typical switching energy versus temperature

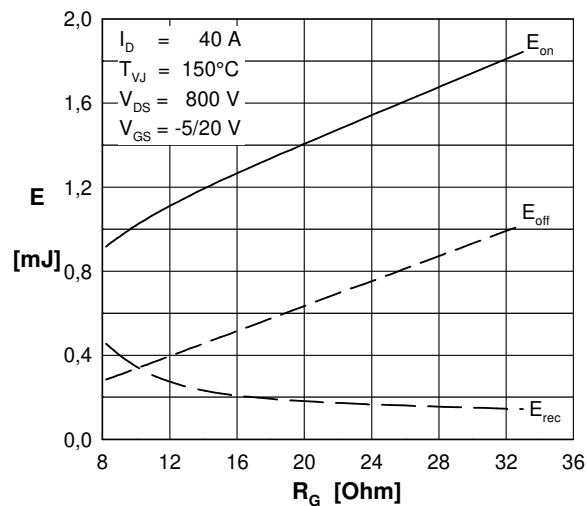


Fig. 15 Typical switching energy versus external gate resistor

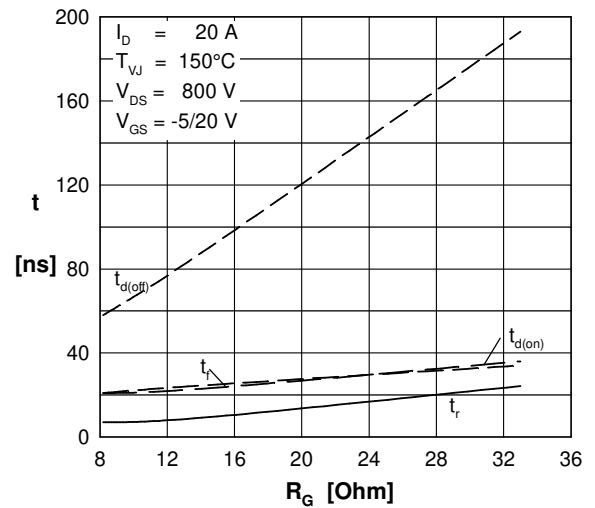


Fig. 16 Typical switching time versus external gate resistor

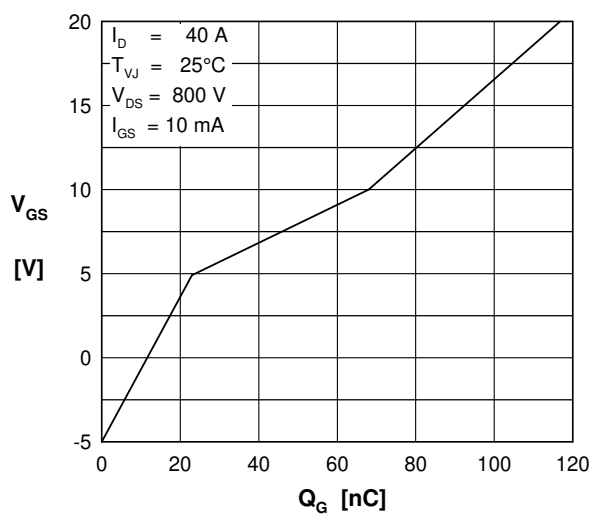


Fig. 17 Typical turn on gate charge, trendline

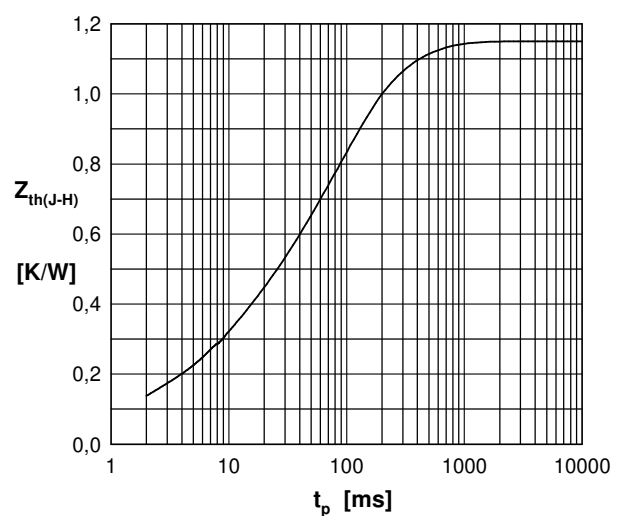


Fig. 18 Typical transient thermal impedance